

JC17 Rec'd PCT/US 23 JUN 2005

FORM PTO 1449 (modified) U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE LIST OF REFERENCES CITED BY APPLICANT(S) (Use several sheets if necessary)			ATTY DOCKET NO.		APPLICATION NO.		
			00862.102568.		U.S. National Stage of PCT/JP2004/018982; filed December 14, 2004		
			APPLICANT		KAZUYA NOTSU, ET AL.		
			FILING DATE	Not Yet Assigned	GROUP	3818 Not Yet Assigned	
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*EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
<i>[Signature]</i>		5,221,413	06/22/93	Brasen et al.	117	89	
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<i>[Signature]</i>		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES/NO/ OR ABSTRACT
<i>[Signature]</i>		EP 1 248 294 A2	10/09/02	EPO			
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EXAMINER	<i>[Signature]</i>	DATE CONSIDERED		10/06			

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

FORM PTO 1449 (modified)			ATTY DOCKET NO. 00862.102568.	APPLICATION NO. 10/540,261		
U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE			APPLICANT KAZUYA NOTSU, ET AL.			
LIST OF REFERENCES CITED BY APPLICANT(S) (Use several sheets if necessary)			FILING DATE 10/540,261	GROUP <i>2815</i>		
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EXAMINER <i>Doherty</i>	DATE CONSIDERED <i>10/06</i>					

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